NTMFS4C05N

MOSFET – Power, Single, N-Channel, SO-8 FL
30 V, 78 A

Features
- Low $R_{DS(on)}$ to Minimize Conduction Losses
- Low Capacitance to Minimize Driver Losses
- Optimized Gate Charge to Minimize Switching Losses
- These Devices are Pb−Free, Halogen Free/BFR Free and are RoHS Compliant

Applications
- CPU Power Delivery
- DC−DC Converters

MAXIMUM RATINGS (T_J = 25°C unless otherwise stated)

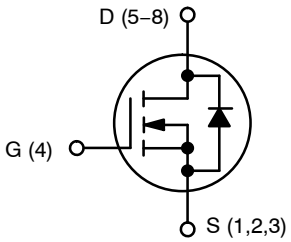
Parameter			Symbol	Value	Unit
Drain−to−Source Voltage			V_{DSS}	30	V
Gate−to−Source Voltage			V_{GS}	±20	V
Continuous Drain Current $R_{\theta JA}$ (Note 1)	Steady State	T_A = 25°C	I_D	21.7	A
		T_A = 80°C		16.3	
Power Dissipation $R_{\theta JA}$ (Note 1)		T_A = 25°C	P_D	2.57	W
Continuous Drain Current $R_{\theta JA} \le 10$ s (Note 1)		T_A = 25°C	I_D	34.8	A
		T_A = 80°C		26.0	
Power Dissipation $R_{\theta JA} \le 10$ s (Note 1)		T_A = 25°C	P_D	6.6	W
Continuous Drain Current $R_{\theta JA}$ (Note 2)		T_A = 25°C	I_D	11.9	A
		T_A = 80°C		8.9	
Power Dissipation $R_{\theta JA}$ (Note 2)		T_A = 25°C	P_D	0.77	W
Continuous Drain Current $R_{\theta JC}$ (Note 1)		T_C = 25°C	I_D	78	A
		T_C =80°C		58	
Power Dissipation $R_{\theta JC}$ (Note 1)		T_C = 25°C	P_D	33	W
Pulsed Drain Current	T_A = 25°C, t_p = 10 μs		I_{DM}	174	A
Current Limited by Package		T_A = 25°C	I_{Dmax}	80	A
Operating Junction and Storage Temperature			T_J, T_{STG}	−55 to +150	°C
Source Current (Body Diode)			I_S	30	A
Drain to Source dV/dt			dV/d_t	7.0	V/ns
Single Pulse Drain−to−Source Avalanche Energy (T_J = 25°C, V_{GS} = 20 V, I_L = 41 A_{pk}, L = 0.1 mH, R_{GS} = 25 Ω) (Note 3)			E_{AS}	84	mJ
Lead Temperature for Soldering Purposes (1/8″ from case for 10 s)			T_L	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.
1. Surface−mounted on FR4 board using 1 sq−in pad, 1 oz Cu.

ON Semiconductor®

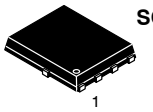
www.onsemi.com

$V_{(BR)DSS}$	$R_{DS(ON)}$ MAX	I_D MAX
30 V	3.4 mΩ @ 10 V	78 A
	5.0 mΩ @ 4.5 V	

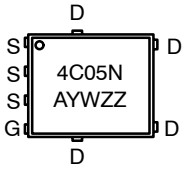


N−CHANNEL MOSFET

MARKING DIAGRAMS



SO−8 FLAT LEAD CASE 488AA STYLE 1



A = Assembly Location
Y = Year
W = Work Week
ZZ = Lot Traceabililty

ORDERING INFORMATION

Device	Package	Shipping†
NTMFS4C05NT1G	SO−8 FL (Pb−Free)	1500 / Tape & Reel
NTMFS4C05NT3G	SO−8 FL (Pb−Free)	5000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

2. Surface−mounted on FR4 board using the minimum recommended pad size.
3. This is the absolute maximum ratings. Parts are 100% tested at T_J = 25°C, V_{GS} = 20 V, I_L = 29 A, E_{AS} = 42 mJ.

THERMAL RESISTANCE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Junction−to−Case (Drain)	$R_{\theta JC}$	3.8	°C/W
Junction−to−Ambient − Steady State (Note 4)	$R_{\theta JA}$	48.6	
Junction−to−Ambient − Steady State (Note 5)	$R_{\theta JA}$	161.7	
Junction−to−Ambient − (t ≤ 10 s) (Note 4)	$R_{\theta JA}$	19	

4. Surface−mounted on FR4 board using 1 sq−in pad, 1 oz Cu.
5. Surface−mounted on FR4 board using the minimum recommended pad size.

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise specified)

Parameter	Symbol	Test Condition		Min	Typ	Max	Unit
OFF CHARACTERISTICS							
Drain−to−Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0 V, I_D = 250 μA		30			V
Drain−to−Source Breakdown Voltage (transient)	$V_{(BR)DSSt}$	V_{GS} = 0 V, $I_{D(aval)}$ = 12.6 A, T_{case} = 25°C, $t_{transient}$ = 100 ns		34			V
Drain−to−Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}$/T_J				12		mV/°C
Zero Gate Voltage Drain Current	I_{DSS}	V_{GS} = 0 V, V_{DS} = 24 V	T_J = 25°C			1.0	μA
			T_J = 125°C			10	
Gate−to−Source Leakage Current	I_{GSS}	V_{DS} = 0 V, V_{GS} = ±20 V				±100	nA
ON CHARACTERISTICS (Note 6)							
Gate Threshold Voltage	$V_{GS(TH)}$	V_{GS} = V_{DS}, I_D = 250 μA		1.3		2.2	V
Negative Threshold Temperature Coefficient	$V_{GS(TH)}/T_J$				5.1		mV/°C
Drain−to−Source On Resistance	$R_{DS(on)}$	V_{GS} = 10 V	I_D = 30 A		2.7	3.4	mΩ
		V_{GS} = 4.5 V	I_D = 30 A		4.0	5.0	
Forward Transconductance	g_{FS}	V_{DS} = 1.5 V, I_D = 15 A			68		S
Gate Resistance	R_G	T_A = 25°C		0.3	1.0	2.0	Ω
CHARGES AND CAPACITANCES							
Input Capacitance	C_{ISS}	V_{GS} = 0 V, f = 1 MHz, V_{DS} = 15 V			1972		pF
Output Capacitance	C_{OSS}				1215		
Reverse Transfer Capacitance	C_{RSS}				59		
Capacitance Ratio	C_{RSS}/C_{ISS}	V_{GS} = 0 V, V_{DS} = 15 V, f = 1 MHz			0.030		
Total Gate Charge	$Q_{G(TOT)}$	V_{GS} = 4.5 V, V_{DS} = 15 V; I_D = 30 A			14		nC
Threshold Gate Charge	$Q_{G(TH)}$				3.3		
Gate−to−Source Charge	Q_{GS}				6.0		
Gate−to−Drain Charge	Q_{GD}				5.0		
Gate Plateau Voltage	V_{GP}				3.1		V
Total Gate Charge	$Q_{G(TOT)}$	V_{GS} = 10 V, V_{DS} = 15 V; I_D = 30 A			30		nC
SWITCHING CHARACTERISTICS (Note 7)							
Turn−On Delay Time	$t_{d(ON)}$	V_{GS} = 4.5 V, V_{DS} = 15 V, I_D = 15 A, R_G = 3.0 Ω			11		ns
Rise Time	t_r				32		
Turn−Off Delay Time	$t_{d(OFF)}$				21		
Fall Time	t_f				7.0		

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise specified)

Parameter	Symbol	Test Condition		Min	Typ	Max	Unit
SWITCHING CHARACTERISTICS (Note 7)							
Turn−On Delay Time	$t_{d(ON)}$	V_{GS} = 10 V, V_{DS} = 15 V, I_D = 15 A, R_G = 3.0 Ω			8.0		ns
Rise Time	t_r				26		
Turn−Off Delay Time	$t_{d(OFF)}$				26		
Fall Time	t_f				5.0		
DRAIN−SOURCE DIODE CHARACTERISTICS							
Forward Diode Voltage	V_{SD}	V_{GS} = 0 V, I_S = 10 A	T_J = 25°C		0.77	1.1	V
			T_J = 125°C		0.62		
Reverse Recovery Time	t_{RR}	V_{GS} = 0 V, dI_S/dt = 100 A/μs, I_S = 30 A			40.2		ns
Charge Time	t_a				20.3		
Discharge Time	t_b				19.9		
Reverse Recovery Charge	Q_{RR}				30.2		nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

6. Pulse Test: pulse width ≤ 300 μs, duty cycle ≤ 2%.
7. Switching characteristics are independent of operating junction temperatures.

TYPICAL CHARACTERISTICS

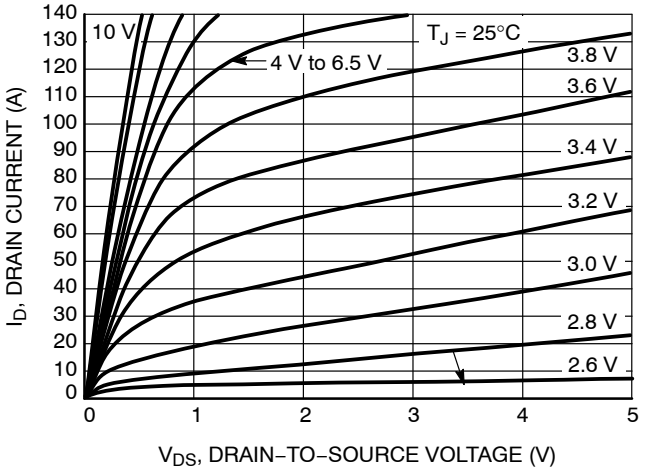


Figure 1. On−Region Characteristics

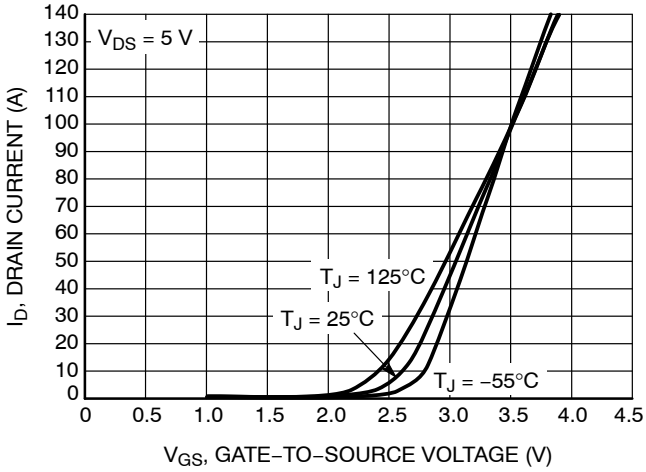


Figure 2. Transfer Characteristics

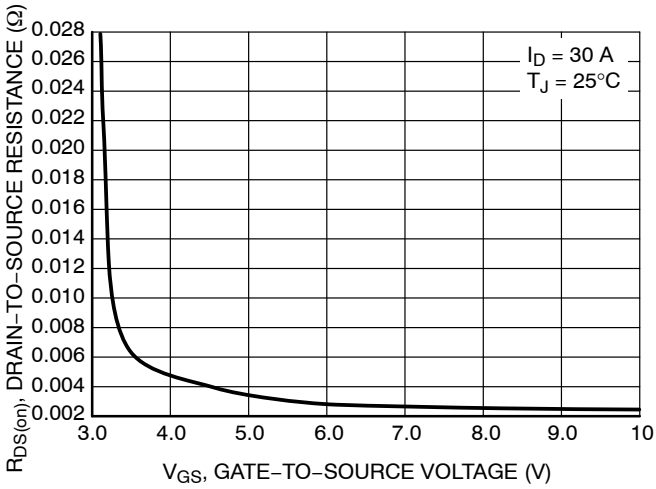


Figure 3. On−Resistance vs. V_{GS}

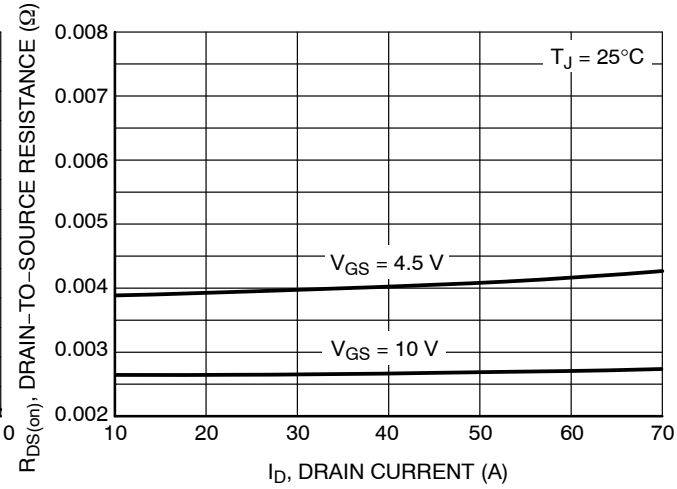


Figure 4. On−Resistance vs. Drain Current and Gate Voltage

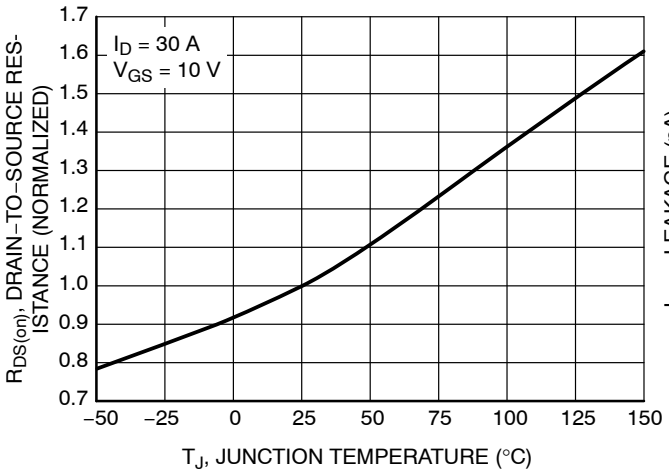


Figure 5. On−Resistance Variation with Temperature

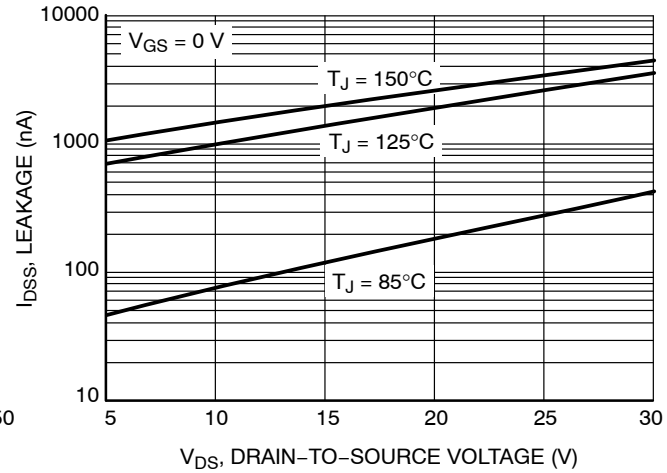


Figure 6. Drain−to−Source Leakage Current vs. Voltage

TYPICAL CHARACTERISTICS

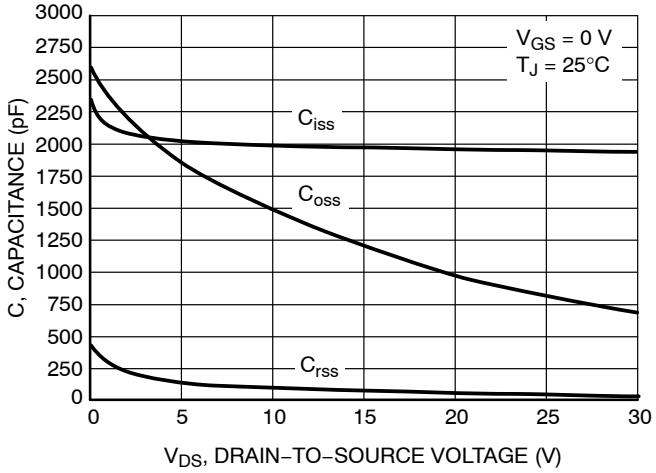


Figure 7. Capacitance Variation

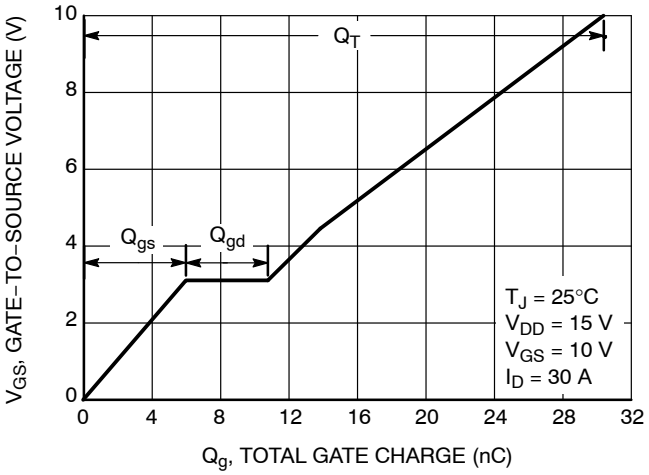


Figure 8. Gate−to−Source and Drain−to−Source Voltage vs. Total Charge

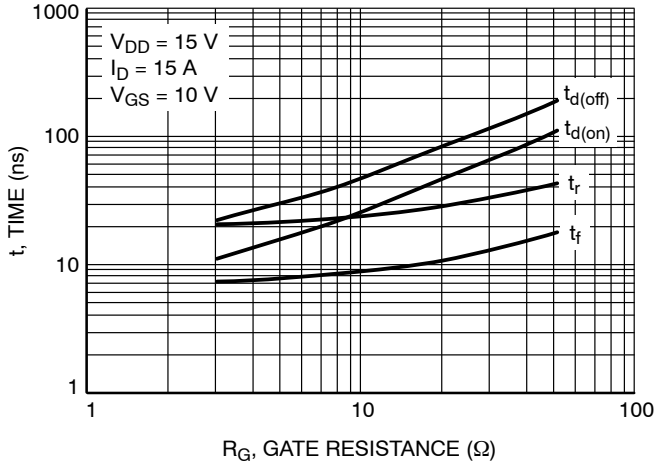


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

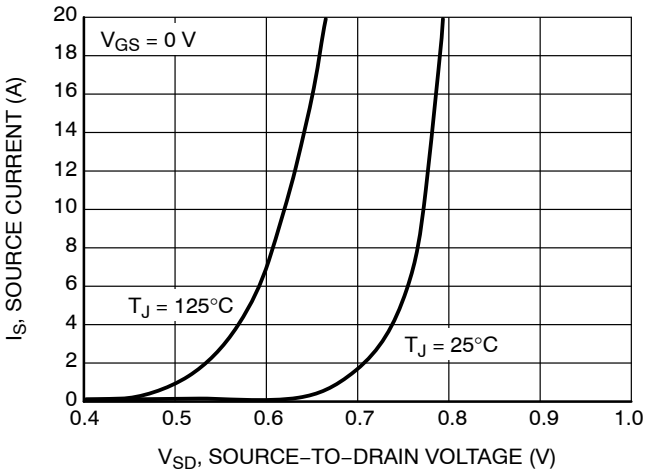


Figure 10. Diode Forward Voltage vs. Current

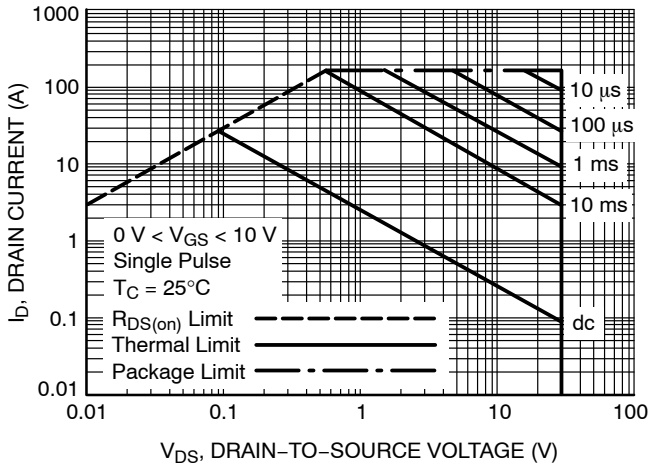


Figure 11. Maximum Rated Forward Biased Safe Operating Area

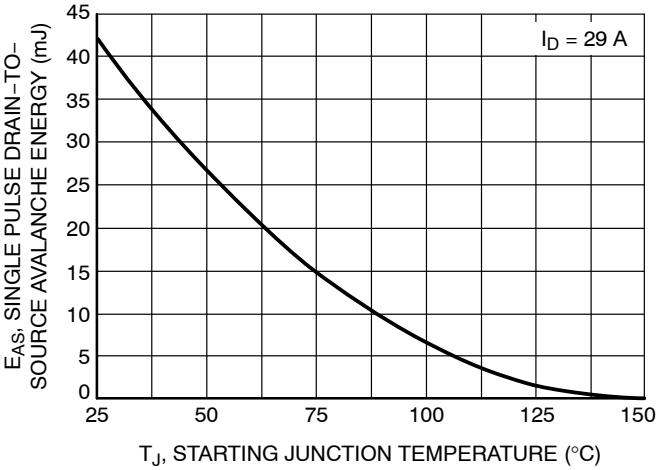


Figure 12. Maximum Avalanche Energy vs. Starting Junction Temperature

TYPICAL CHARACTERISTICS

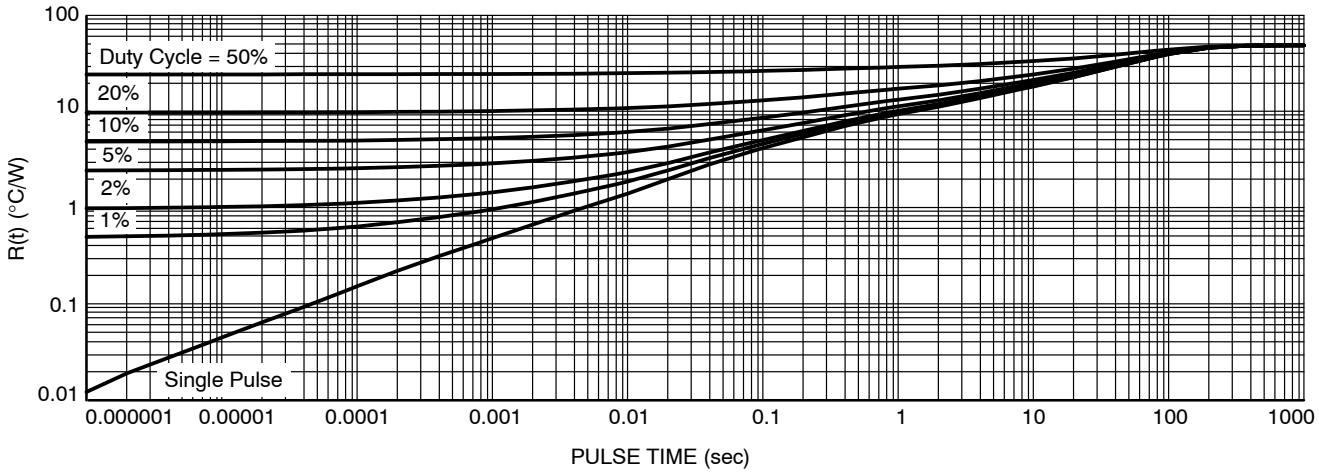


Figure 13. Thermal Response

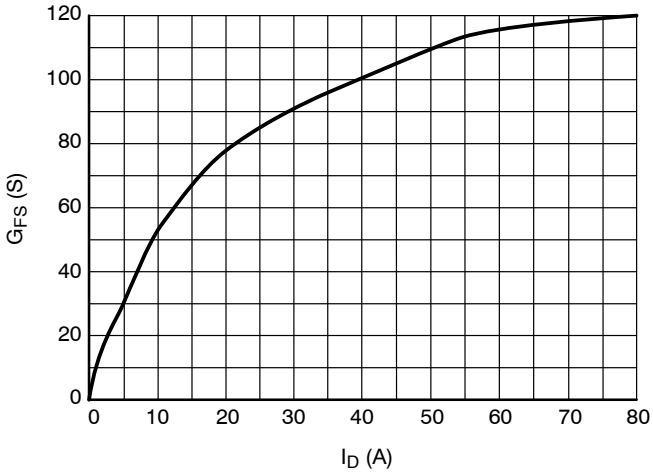


Figure 14. G_{FS} vs. I_D

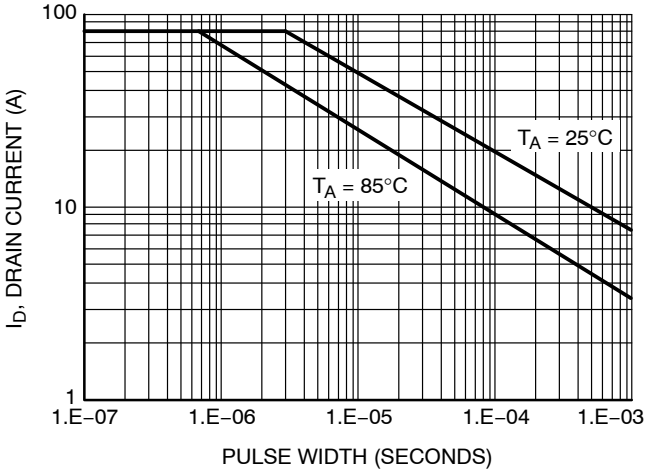
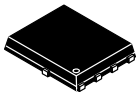


Figure 15. Avalanche Characteristics

MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS

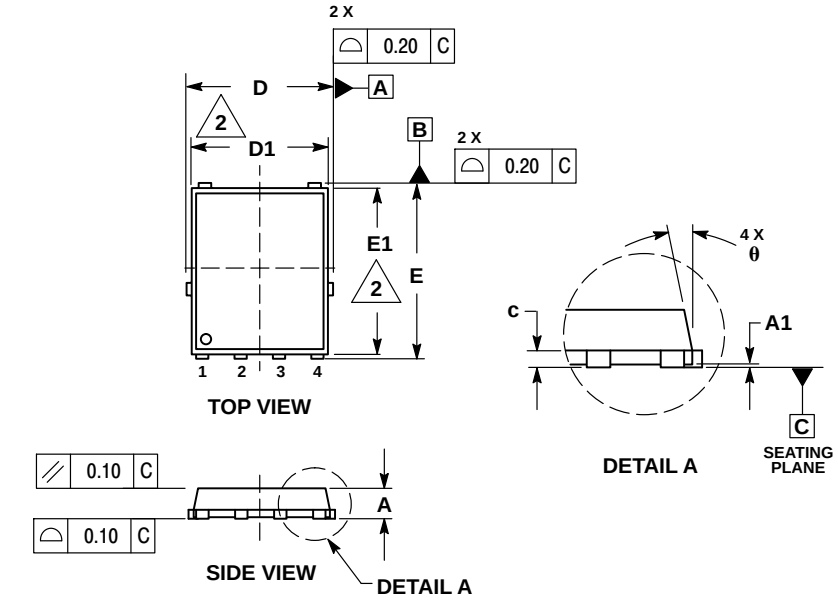
ON Semiconductor®



SCALE 2:1

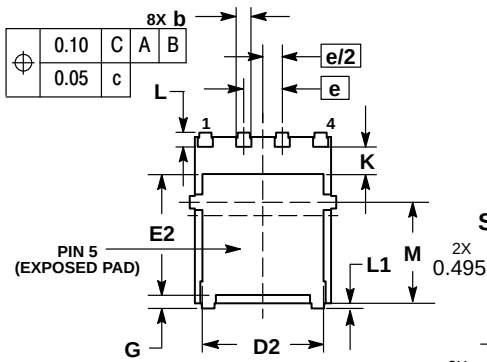
DFN5 5x6, 1.27P
(SO−8FL)
CASE 488AA
ISSUE N

DATE 25 JUN 2018

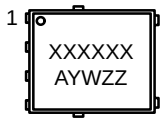


NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION D1 AND E1 DO NOT INCLUDE MOLD FLASH PROTRUSIONS OR GATE BURRS.

	MILLIMETERS		
DIM	MIN	NOM	MAX
A	0.90	1.00	1.10
A1	0.00	–––	0.05
b	0.33	0.41	0.51
c	0.23	0.28	0.33
D	5.00	5.15	5.30
D1	4.70	4.90	5.10
D2	3.80	4.00	4.20
E	6.00	6.15	6.30
E1	5.70	5.90	6.10
E2	3.45	3.65	3.85
e	1.27 BSC		
G	0.51	0.575	0.71
K	1.20	1.35	1.50
L	0.51	0.575	0.71
L1	0.125 REF		
M	3.00	3.40	3.80
θ	0 °	–––	12 °



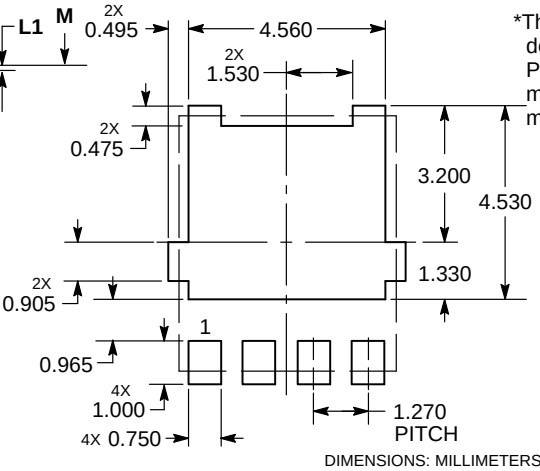
GENERIC MARKING DIAGRAM*



XXXXXX = Specific Device Code
A = Assembly Location
Y = Year
W = Work Week
ZZ = Lot Traceability

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “ ▪”, may or may not be present. Some products may not follow the Generic Marking.

RECOMMENDED SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

STYLE 1:
PIN 1. SOURCE
2. SOURCE
3. SOURCE
4. GATE
5. DRAIN

STYLE 2:
PIN 1. ANODE
2. ANODE
3. ANODE
4. NO CONNECT
5. CATHODE

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

DOCUMENT NUMBER:	**98AON14036D**	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped “CONTROLLED COPY” in red.
DESCRIPTION:	**DFN5 5x6, 1.27P (SO−8FL)**	**PAGE 1 OF 1**

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Email Requests to: orderlit@onsemi.com

onsemi Website: www.onsemi.com

TECHNICAL SUPPORT
North American Technical Support:
Voice Mail: 1 800−282−9855 Toll Free USA/Canada
Phone: 011 421 33 790 2910

Europe, Middle East and Africa Technical Support:
Phone: 00421 33 790 2910
For additional information, please contact your local Sales Representative

◊

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for MOSFET ***category:***

Click to view products by ON Semiconductor ***manufacturer:***

Other Similar products are found below :

614233C 648584F IRFD120 JANTX2N5237 FCA20N60_F109 FDZ595PZ 2SK2545(Q,T) 405094E 423220D TPCC8103,L1Q(CM MIC4420CM-TR VN1206L SBVS138LT1G 614234A 715780A NTNS3166NZT5G SSM6J414TU,LF(T 751625C BUK954R8-60E NTE6400 SQJ402EP-T1-GE3 2SK2614(TE16L1,Q) 2N7002KW-FAI DMN1017UCP3-7 EFC2J004NUZTDG ECH8691-TL-W FCAB21350L1 P85W28HP2F-7071 DMN1053UCP4-7 NTE221 NTE222 NTE2384 NTE2903 NTE2941 NTE2945 NTE2946 NTE2960 NTE2967 NTE2969 NTE2976 NTE455 NTE6400A NTE2910 NTE2916 NTE2956 NTE2911 DMN2080UCB4-7 TK10A80W,S4X(S SSM6P69NU,LF DMP22D4UFO-7B